

IN THE CLAIMS:

Claims 1-42 (Previously Cancelled).

43. (Amended) A stress-adjusted insulating film forming method for forming a stress-adjusted multilayered insulating film on a substrate, said method comprising:

- (a) forming a first insulating layer with compressive stress;
- (b) forming an aluminum interconnection layer on and in contact with said first insulating layer;
- (c) forming a second insulating layer with compressive stress on and in contact with said interconnection layer;

wherein said interconnection layer is sandwiched between and in contact with said first insulating layer and said second insulating layer ~~and wherein the total stress in said insulating layers is limited to less than 2×10^5 dyne/cm so as to suppress bending of said interconnection layer;~~ and

- (d) before forming said first insulating layer or after forming said second insulating layer, forming a third insulating layer with tensile stress ~~, so as to adjust overall stress of said stress-adjusted insulating film;~~

wherein the stress-adjusted insulating film has first through i-th insulating layers having the thickness t_1 through t_i , respectively, ~~and~~ wherein the thickness (t_i) of i-th insulating layer of said stress-adjusted film is determined so that the total ~~as not to exceed~~ stress (σ_T) of said overall stress-adjusted multilayered insulating film is less than $+2 \times 10^5$ dyne/cm, wherein said total

where said stress (σ_T) is calculated as:

$$\sigma_T = \sum_{i=1}^n (t_i X \sigma_i)$$

and wherein (σ_i) is stress in said i-th insulating film and is positive when tensile stress and negative when compressive stress.

Claims 44-46 (Previously cancelled).

47. (Previously Amended) A method according to claim 43, wherein said forming of said first insulating layer is by plasma CVD, and said forming of said second insulating film is by heating for reaction of a gaseous mixture including at least an organic silane and oxygen.

Claims 48-52 (Previously cancelled).

53. (Newly added) A method according to claim 43 wherein said steps (a) - (d) are repeated to produce a stress-adjusted multilayered insulating film wherein adjacent aluminum interconnection layers are separated by, in sequence, a first insulating layer, a third insulating layer and a second insulating layer.